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Description

The TS5A3359 is a single-pole triple-throw (SP3T) analog switch that is designed to operate from 1.65 V to 5.5 V. The device offers a low ON-state resistance and excellent ON-state resistance matching with the break-before-make feature, to prevent signal distortion during the transferring of a signal from one channel to another. The device has an excellent total harmonic distortion (THD) performance and consumes very low power. These features make this device suitable for portable audio applications.

Applications

- Cell Phones
- PDAs
- Portable Instrumentation
- Audio and Video Signal Routing
- Low-Voltage Data Acquisition Systems
- Communication Circuits
- Modems
- Hard Drives
- Computer Peripherals
- Wireless Terminals and Peripherals

YEP OR YZP PACKAGE DCT OR DCU PACKAGE (BOTTOM VIEW) (TOP VIEW) Logic 8 V₊ (5) NO0 GND IN₂ Control 7 COM 6 IN₁ NO1 COM NO2 6 IN1 Logic Contro (8) **GND**

FUNCTION TABLE

IN2	IN1	COM TO NO, NO TO COM
L	NL -L	OFF
L	Н	COM = NO0
H	Old Mari	COM = NO1
H H	Н	COM = NO2

Features

- Isolation in the Power-Down Mode, V₊ = 0
- Specified Break-Before-Make Switching
- Low ON-State Resistance (1 Ω)
- Control Inputs Are 5.5-V Tolerant
- Low Charge Injection
- Excellent ON-State Resistance Matching
- Low Total Harmonic Distortion (THD)
- 1.65-V to 5.5-V Single-Supply Operation
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 1000-V Charged-Device Model (C101)

Summary of Characteristics

 $V_{1} = 5 V_{1} T_{A} = 25^{\circ}C_{1}$

$V_{+} = 5 \text{ V}, I_{A} = 25 \text{ C}$	N.L. P.
Configuration	Triple 3:1 Multiplexer/ Demultiplexer (1 × SP3T)
Number of channels	1
ON-state resistance (ron)	1.1 Ω
ON-state resistance match (Δr _{ON})	0.1 Ω
ON-state resistance flatness (ron(flat))	0.15 Ω
Turn-on/turn-off time (tON/tOFF)	40 ns/35 ns
Break-before-make time (t _{BBM})	1 ns
Charge injection (Q _C)	40 pC
Bandwidth (BW)	100 MHz
OFF isolation (OISO)	-65 dB at 1 MHz
Crosstalk (XTALK)	-66 dB at 1 MHz
Total harmonic distortion (THD)	0.01%
Leakageourrent(ICOM(OFF)/INO(OFF))	±20 nA
Power-supply current (I ₊)	0.1 μΑ
Package option	8-pin, DCT, DCU, YEP, or YZP



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ORDERING INFORMATION

TA	PACKAGE(1)	PACKAGE ⁽¹⁾ ORDERABLE PART NUMBER		TOP-SIDE MARKING(2)
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Townson	TS5A3359YEPR	DDE///EW
−40°C to 85°C	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and reel	TS5A3359YZPR	PREVIEW
	SSOP - DCT	Tape and reel	TS5A3359DCTR	PREVIEW
	VSSOP - DCU	Tape and reel	TS5A3359DCUR	JAL_

⁽¹⁾ Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

Absolute Minimum and Maximum Ratings(1)(2)

over operating free-air temperature range (unless otherwise noted)

•			MIN	MAX	UNIT
٧+	Supply voltage range(3)		-0.5	6.5	V
V _{NO}	Analog voltage range(3)(4)(5)		-0.5	V ₊ + 0.5	V
lΚ	Analog port diode current	V _{NO} , V _{COM} < 0	-50		mA
INO	On-state switch current	V V 045 V	-200	200	^
ICOM	On-state peak switch current(6)	V_{NO} , $V_{COM} = 0$ to V_+	-400	400	mA
VI	Digital input voltage range(3)(4)	·	-0.5	6.5	V
lıK	Digital input clamp current	V _I < 0	-50		mA
I ₊	Continuous current through V+			100	^
IGND	Continuous current through GND		-100	100	mA
	5	DCT/DCU package		227	0044
θJΑ	Package thermal impedance(7)	YEP/YZP package		140	°C/W
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Pulse at 1-ms duration < 10% duty cycle.
- (7) The package thermal impedance is calculated in accordance with JESD 51-7.

⁽²⁾ DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site.

DCU: The actual top-side marking has one additional character that designates the assembly/test site.



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Electrical Characteristics for 5-V Supply(1)

 $V_{+} = 4.5 \text{ V}$ to 5.5 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		TA	٧+	MIN	TYP	MAX	UNIT
Analog Switch	•				ı.				
Analog signal range	V _{COM} , V _{NO}					0		V ₊	V
Peak ON resistance	r _{peak}	$0 \le (V_{NO}) \le V_{+},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 13	25 °C Full	4.5 V		0.8	1.1 1.5	Ω
ON-state resistance	r _{on}	V _{NO} = 2.5 V, I _{COM} = -100 mA,	Switch ON, See Figure 13	25°C Full	4.5 V		0.7	0.9	Ω
ON-state resistance match between channels	Δr _{on}	V _{NO} = 2.5 V, I _{COM} = -100 mA,	Switch ON, See Figure 13	25°C Full	4.5 V		0.1	0.1	Ω
ON-state		$0 \le (V_{NO}) \le V_{+},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 13	25°C			0.15		
resistance flatness	ron(flat)	V _{NO} = 1 V, 1.5 V, 2.5 V, I _{COM} = -100 mA,	Switch ON, See Figure 13	25°C Full	4.5 V		0.1	0.25 0.25	Ω
		$V_{NO} = 1 \text{ V}, V_{COM} = 1 \text{ V to } 4.5 \text{ V},$	Switch OFF,	25°C		-20	5	20	
NO OFF leakage	INO(OFF)	or $V_{NO} = 4.5 \text{ V}, V_{COM} = 1 \text{ V to } 4.5 \text{ V},$	See Figure 14	Full	5.5 V	-150		150	nA
current	NO(PWROFF)	$V_{NO} = 0 \text{ to } 5.5 \text{ V},$	Switch OFF,	25°C	0 V	-1	8.0	1	μA
NO		V _{COM} = 5.5 V to 0, V _{NO} = 1 V, V _{COM} = Open,	See Figure 14	Full 25°C		-25 -30	5	25 30	·
ON leakage current	INO(ON)	or V _{NO} = 4.5 V, V _{COM} = Open,	Switch ON, See Figure 15	Full	5.5 V	-220		220	nA
	loov(o==)	$V_{NO} = 4.5 \text{ V}, V_{COM} = 1 \text{ V to } 4.5 \text{ V},$	Switch OFF,	25°C	5.5 V	-25	8	25	nA
COM OFF leakage	ICOM(OFF)	$V_{NO} = 1 \text{ V}, V_{COM} = 1 \text{ V to } 4.5 \text{ V},$	See Figure 14	Full	5.5 V	-250		250	IIA
current	COM(PWROFF)	V _{COM} = 0 to 5.5 V, V _{NO} = 5.5 V to 0,	Switch OFF, See Figure 14	25°C	0 V	-8 50	0.1	8	μΑ
COM		V _{NO} = 0.5 v to 0, V _{NO} = 0pen, V _{COM} = 1 V,		Full 25°C		-50 -30	5	30	
ON leakage current	ICOM(ON)	or V _{NO} = Open, V _{COM} = 4.5 V,	Switch ON, See Figure 15	Full	5.5 V	-220		220	nA
Digital Control Inpu	uts (IN1, IN2)(2)	l .		•					
Input logic high	VIH			Full		2.4		5.5	V
Input logic low	V _{IL}			Full		0		0.8	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	5.5 V	-2 -20		20	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



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Electrical Characteristics for 5-V Supply⁽¹⁾ (continued) $V_+ = 4.5 \text{ V to } 5.5 \text{ V}, T_A = -40^{\circ}\text{C to } 85^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST COI	NDITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	4	V _{COM} = V ₊ ,	C _L = 35 pF,	25°C	5 V	1	2.5	21	20
rum-on time	tON	$R_L = 50 \Omega$,	See Figure 17	Full	4.5 V to 5.5 V	1		23.5	ns
Turn-off time	torr	$V_{COM} = V_+,$	$C_L = 35 \text{ pF},$	25°C	5 V	1	6	10.5	ns
Tarri on time	tOFF	$R_L = 50 \Omega$,	See Figure 17	Full	4.5 V to 5.5 V	1		12	115
Break-before-	topus	$V_{NO} = V_{+}$	$C_{L} = 35 \text{ pF},$	25°C	5 V	0.5	8.5	18	ns
make time	^t BBM	$R_L = 50 \Omega$,	See Figure 18	Full	4.5 V to 5.5 V	0.5		23	113
Charge injection	QC	$V_{GEN} = 0,$ $R_{GEN} = 0,$	C _L = 1 nF, See Figure 22	25°C	5 V		20		рC
NO OFF capacitance	C _{NO(OFF)}	V _{NO} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	5 V		18		pF
COM OFF capacitance	CCOM(OFF)	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	2.5 V		54		pF
NO ON capacitance	C _{NO(ON)}	V _{NO} = V ₊ or GND, Switch ON,	See Figure 16	25°C	5 V		78		pF
COM ON capacitance	CCOM(ON)	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	5 V		78		pF
Digital input capacitance	Cl	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	5 V		2.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	5 V		75		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 20	25°C	5 V		-64		dB
Crosstalk	XTALK	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 21	25°C	5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega$, $C_L = 50 pF$,	f = 20 Hz to 20 kHz, See Figure 23	25°C	5 V		0.005		%
Supply					•				
Positive supply		V V or CND	Switch ON or OFF	25°C	F.F.V		16	50	π Λ
current	I ₊	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	Full	5.5 V			1200	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum



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Electrical Characteristics for 3.3-V Supply⁽¹⁾ $V_+ = 3 \text{ V to } 3.6 \text{ V}, T_A = -40 ^{\circ}\text{C to } 85 ^{\circ}\text{C (unless otherwise noted)}$

PARAMETER	SYMBOL	TEST CONDITIONS		TA	٧+	MIN	TYP	MAX	UNIT
Analog Switch	•								
Analog signal range	V _{COM} , V _{NO} , V _{NC}					0		٧+	V
Peak ON resistance	^r peak	$0 \le (V_{NO}) \le V_+,$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 13	25 °C Full	3 V		1.3	1.6	Ω
ON-state resistance	r _{on}	V _{NO} = 2 V, I _{COM} = -100 mA,	Switch ON, See Figure 13	25°C Full	3 V		1.2	1.6 1.8	Ω
ON-state resistance match between channels	Δr _{on}	V _{NO} = 2 V, 0.8 V, I _{COM} = -100 mA,	Switch ON, See Figure 13	25°C Full	3 V		0.1	0.15 0.15	Ω
ON-state		$0 \le (V_{NO}) \le V_{+},$ $I_{COM} = -100 \text{ mA},$	Switch ON, See Figure 13	25°C			0.2		
resistance flatness	ron(flat)	V _{NO} = 2 V, 0.8 V, I _{COM} = -100 mA,	Switch ON, See Figure 13	25°C Full	3 V		0.2	0.35 0.35	Ω
		$V_{NO} = 1 \text{ V}, V_{COM} = 1 \text{ V to 3 V},$	Switch OFF,	25°C		-15	3	15	
NO OFF leakage	INO(OFF)	or V _{NO} = 3 V, V _{COM} = 1 V to 3 V,	See Figure 14	Full	3.6 V	-30		30	nA
current		$V_{NO} = 0 \text{ to } 3.6 \text{ V},$	Switch OFF,	25°C	0.17	-1	0.2	1	
	NO(PWROFF)	$V_{COM} = 3.6 \text{ V to } 0,$	See Figure 14	Full	0 V	-10		10	μΑ
NO ON lookogo	1	V _{NO} = 1 V, V _{COM} = Open,	Switch ON,	25°C	201	-15	3	15	A
ON leakage current	INO(ON)	$V_{NO} = 3 \text{ V}, V_{COM} = \text{Open},$	See Figure 15	Full	3.6 V	-40		40	nA
		$V_{NO} = 0 \text{ V to } 3.6 \text{ V}, V_{COM} = 1 \text{ V},$	Switch OFF,	25°C	0.01/	-15	3	15	
COM OFF leakage	ICOM(OFF)	$V_{NO} = 3.6 \text{ V to 0 V, V}_{COM} = 3 \text{ V,}$	See Figure 14	Full	3.6 V	-75		75	nA
current		V _{COM} = 0 to 3.6 V,	Switch OFF,	25°C	0.1/	-1	0.2	1	^
	COM(PWROFF)	$V_{NO} = 3.6 V \text{ to } 0,$	See Figure 14	Full	0 V	-20		20	μΑ
COM		$V_{NO} = Open, V_{COM} = 1 V,$	Switch ON,	25°C	0.01/	-15	4	15	4
ON leakage current	ICOM(ON)	or V _{NO} = Open, V _{COM} = 3 V,	See Figure 15	Full	3.6 V	-40		40	nA
Digital Control Inpu	uts (IN1, IN2)(2)				•				
Input logic high	VIH			Full		2		5.5	V
Input logic low	V _{IL}			Full		0		0.8	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	3.6 V	-2 -20		20	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V+ or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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Electrical Characteristics for 3.3-V Supply⁽¹⁾ (continued) $V_+ = 3 \ V$ to 3.6 V, $T_A = -40 \ C$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CO	NDITIONS	TA	٧+	MIN	TYP	MAX	UNIT
Dynamic						-			
Turn-on time		V _{COM} = V ₊ ,	C _L = 35 pF,	25°C	3.3 V	1	16	30.5	
rum-on time	tON	$R_L = 50 \Omega$,	See Figure 17	Full	3 V to 3.6 V	1		34	ns
Turn-off time	4	V _{COM} = V ₊ ,	C _L = 35 pF,	25°C	3.3 V	1	6	11.5	
rum-on ume	tOFF	$R_L = 50 \Omega$,	See Figure 17	Full	3 V to 3.6 V	1		12.5	ns
Break-before-	toour	$V_{NC} = V_{NO} = V_+,$	$C_L = 35 pF$,	25°C	3.3 V	0.5	13	26	20
make time	^t BBM	$R_L = 50 \Omega$,	See Figure 18	Full	3 V to 3.6 V	0.5		30	ns
Charge injection	QC	V _{GEN} = 0, R _{GEN} = 0,	$C_L = 1 \text{ nF},$ See Figure 22	25°C	3.3 V		12		рC
NO OFF capacitance	C _{NO(OFF)}	V _{NO} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	3.3 V		18		pF
COM OFF capacitance	C _{COM(OFF)}	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	3.3 V		55		pF
NO ON capacitance	C _{NO(ON)}	V _{NO} = V ₊ or GND, Switch ON,	See Figure 16	25°C	3.3 V		78		pF
COM ON capacitance	CCOM(ON)	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	3.3 V		78		pF
Digital input capacitance	Cl	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	3.3 V		2.5		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	3.3 V		73		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 20	25°C	3.3 V		-64		dB
Crosstalk	XTALK	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 21	25°C	3.3 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega$, $C_L = 50 pF$,	f = 20 Hz to 20 kHz, See Figure 23	25°C	3.3 V		0.010		%
Supply				1	ı				•
Positive supply				25°C			2	20	
current	1+	$V_I = V_+ \text{ or GND},$	Switch ON or OFF	Full	3.6 V			350	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum



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Electrical Characteristics for 2.5-V Supply(1)

 $V_{+} = 2.3 \text{ V}$ to 2.7 V, $T_{A} = -40 ^{\circ}\text{C}$ to 85 $^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		TA	٧+	MIN	TYP	MAX	UNIT
Analog Switch						-			
Analog signal range	V _{COM} , V _{NO}					0		٧+	V
Peak ON resistance	^r peak	$0 \le (V_{NO}) \le V_+,$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 13	25 °C Full	2.3 V		1.8	2.5	Ω
ON-state resistance	r _{on}	V _{NO} = 1.8 V, I _{COM} = -8 mA,	Switch ON, See Figure 13	25°C Full	2.3 V		1.5	2.4	Ω
ON-state resistance		V _{NO} = 1.8 V,	Switch ON,	25°C			0.15	0.2	
match between channels	∆r _{on}	$I_{COM} = -8 \text{ mA},$	See Figure 13	Full	2.3 V			0.2	Ω
ON-state		$0 \le (V_{NO}) \le V_{+},$ $I_{COM} = -8 \text{ mA},$	Switch ON, See Figure 13	25°C			0.6		
resistance flatness	ron(flat)	V _{NO} = 0.8 V, 1.8 V, I _{COM} = -8 mA,	Switch ON, See Figure 13	25°C Full	2.3 V		0.6	1	Ω
		$V_{NO} = 0.5 \text{ V}, V_{COM} = 0.5 \text{ V} \text{ to } 2.3 \text{ V},$	Switch OFF,	25°C	0.71/	-15	3	15	
NO OFF leakage	INO(OFF)	$V_{NO} = 2.3 \text{ V}, V_{COM} = 0.5 \text{ V to } 2.3 \text{ V},$	See Figure 14	Full	2.7 V	-30		30	nA
current	NO(PWROFF)	V _{NO} = 0 to 2.7 V, V _{COM} = 2.7 V to 0,	Switch OFF, See Figure 14	25°C Full	0 V	-1 -10	0.1	10	μΑ
NO	, , ,	$V_{NO} = 0.5 \text{ V}, V_{COM} = \text{Open},$	Switch ON,	25°C		-10 -15	3	15	
ON leakage current	INO(ON)	or $V_{NO} = 2.2 \text{ V}, V_{COM} = \text{Open},$	See Figure 15	Full	2.7 V	-35		35	nA
		$V_{NO} = 0.3 \text{ V to } 2.3 \text{ V, } V_{COM} = 0.5 \text{ V,}$	Switch OFF,	25°C	271/	-15	3	15	
COM OFF leakage	ICOM(OFF)	$V_{NO} = 0.3 \text{ V to } 2.3 \text{ V, } V_{COM} = 2.3 \text{ V,}$	See Figure 14	Full	2.7 V	-60		60	nA
current	COM(PWROFF)	$V_{COM} = 0 \text{ to } 2.7 \text{ V},$	Switch OFF,	25°C	0 V	-1	0.1	1	μА
COM	CONTRACTO	$V_{NO} = 2.7 \text{ V to 0},$	See Figure 14	Full		-10		10	•
COM ON leakage	ICOM(ON)	$V_{NO} = Open, V_{COM} = 0.5 V,$ or	Switch ON, See Figure 15	25°C	2.7 V	-15	3.5	15	nA
current	` '	V _{NO} = Open V, V _{COM} = 2.2 V,	Occ riguic 15	Full		-40		40	
	Inputs (IN1, IN2	2)\ <i>^)</i> 							
Input logic high	VIH			Full		1.8		5.5	V
Input logic low	VIL			Full		0		0.6	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C	2.7 V	1		1	nA
Cuilell				Full		10		10	

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



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Electrical Characteristics for 2.5-V Supply⁽¹⁾ (continued) $V_+ = 2.3 \text{ V}$ to 2.7 V, $T_A = -40 ^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CO	NDITIONS	TA	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	4	V _{COM} = V ₊ ,	C _L = 35 pF,	25°C	2.5 V	2	4.5	43	
rum-on ume	tON	$R_L = 50 \Omega$,	See Figure 17	Full	2.3 V to 2.7 V	2		47.5	ns
Turn-off time	torr	$V_{COM} = V_+,$	$C_L = 35 \text{ pF},$	25°C	2.5 V	2	8.5	11	ns
Turri on time	tOFF	$R_L = 50 \Omega$,	See Figure 17	Full	2.3 V to 2.7 V	2		12.5	115
Break-before-	toow	$V_{NO} = V_{+}$	$C_L = 35 pF$,	25°C	2.5 V	0.5	18.5	38.5	ns
make time	t _{BBM}	$R_L = 50 \Omega$,	See Figure 18	Full	2.3 V to 2.7 V	0.5		43	115
Charge injection	QC	$V_{GEN} = 0,$ $R_{GEN} = 0,$	$C_L = 1 \text{ nF},$ See Figure 22	25°C	2.5 V		8		рС
NO OFF capacitance	C _{NO(OFF)}	$V_{NO} = V_{+}$ or GND, Switch OFF,	See Figure 16	25°C	2.5 V		18.5		pF
COM OFF capacitance	C _{COM(OFF)}	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	2.5 V		55		pF
NO ON capacitance	C _{NO(ON)}	V _{NO} = V ₊ or GND, Switch ON,	See Figure 16	25°C	2.5 V		78		pF
COM ON capacitance	C _{COM} (ON)	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	2.5 V		78		pF
Digital input capacitance	Cl	$V_I = V_+$ or GND,	See Figure 16	25°C	2.5 V		3		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	2.5 V		73		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 20	25°C	2.5 V		-64		dB
Crosstalk	XTALK	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 21	25°C	2.5 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega$, $C_L = 50 pF$,	f = 20 Hz to 20 kHz, See Figure 23	25°C	2.5 V		0.030		%
Supply				1	•				
Positive supply current	I ₊	$V_I = V_+$ or GND,	Switch ON or OFF	25°C Full	2.7 V		1	10 250	nA

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum



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Electrical Characteristics for 1.8-V Supply⁽¹⁾

 $V_{+} = 1.65 \text{ V}$ to 1.95 V, $T_{A} = -40^{\circ}\text{C}$ to 85°C (unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		T_A	٧+	MIN	TYP	MAX	UNIT
Analog Switch	ı			•					
Analog signal range	V _{COM} , V _{NO}								>
Peak ON resistance	^r peak	$0 \le (V_{NO}) \le V_+,$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 13	25 °C Full	1.65 V		5	30	Ω
ON-state resistance	r _{on}	V _{NO} = 1.5 V, I _{COM} = -2 mA,	Switch ON, See Figure 13	25°C Full	1.65 V		2	2.5 3.5	Ω
ON-state resistance		V _{NO} = 1.5 V,	Switch ON,	25°C	4.05.1/		0.15	0.4	
match between channels	∆r _{on}	$I_{COM} = -2 \text{ mA},$	See Figure 13	Full	1.65 V			0.4	Ω
ON-state		$\begin{aligned} 0 &\leq (V_{\mbox{NO}}) \leq V_{\mbox{+}}, \\ I_{\mbox{COM}} &= -2 \mbox{ mA}, \end{aligned}$	Switch ON, See Figure 13	25°C	4.05.1/		5		0
resistance flatness	ron(flat)	$V_{NO} = 0.6 \text{ V}, 1.5 \text{ V},$ $I_{COM} = -2 \text{ mA},$	Switch ON, See Figure 13	25°C Full	1.65 V		4.5	TBD TBD	Ω
		$V_{NO} = 0.3 \text{ V}, V_{COM} = 0.3 \text{ V to } 1.65 \text{ V},$	Switch OFF,	25°C	4.05.1/	-15	3	15	
NO OFF leakage	INO(OFF)	or $V_{NO} = 1.65 \text{ V}, V_{COM} = 0.3 \text{ V} \text{ to } 1.65 \text{ V},$	See Figure 14	Full	1.95 V	-30		30	nA
current	NO(PWROFF)	V _{NO} = 0 to 1.95 V,	Switch OFF,	25°C	0 V	-1	0.1	1	μА
	NO(FVINOIT)	V _{COM} = 1.95 V to 0,	See Figure 14	Full		-15		15	μ
NO ON leakage	I _{NO(ON)}	$V_{NO} = 0.3 \text{ V}, V_{COM} = \text{Open},$	Switch ON,	25°C	1.95 V	-15	3	15	nA
current	140(014)	V _{NO} = 1.65 V, V _{COM} = Open,	See Figure 15	Full		-30		30	
	loovyour	$V_{NO} = 0.3 \text{ V to } 1.65 \text{ V}, V_{COM} = 0.3 \text{ V},$	Switch OFF,	25°C	1.95 V	-15	3	15	nA
COM OFF leakage	ICOM(OFF)	$V_{NO} = 0.3 \text{ V to } 1.65 \text{ V}, V_{COM} = 1.65 \text{ V},$	See Figure 14	Full	1.95 V	-50		50	ш
current	loor way ports	V _{COM} = 0 to 1.95 V,	Switch OFF,	25°C	0 V	-1	0.1	1	μА
	COM(PWROFF)	$V_{NO} = 1.95 V \text{ to } 0,$	See Figure 14	Full	0 0	-10		10	μΑ
COM ON leakage	lagrager	$V_{NO} = Open, V_{COM} = 0.3 V,$	Switch ON,	25°C	1.95 V	-15	3	15	nA
current	ICOM(ON)	V _{NO} = Open, V _{COM} = 1.65 V,	See Figure 15	Full	1.95 V	-30		30	IIA
Digital Control	Inputs (IN1, IN2	2)(2)							
Input logic high	V _{IH}			Full		1.5		5.5	٧
Input logic low	V _{IL}			Full		0		0.6	V
Input leakage current	I _{IH} , I _{IL}	V _I = 5.5 V or 0		25°C Full	1.95 V	-2 20		20	nA
Janon	<u> </u>			ruii		20		20	

⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

⁽²⁾ All unused digital inputs of the device must be held at V₊ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.



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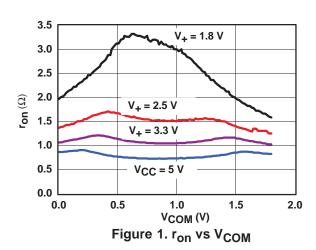
Electrical Characteristics for 1.8-V Supply⁽¹⁾ (continued) $V_+ = 1.65 \text{ V}$ to 1.95 V, $T_A = -40 ^{\circ}\text{C}$ to 85°C (unless otherwise noted)

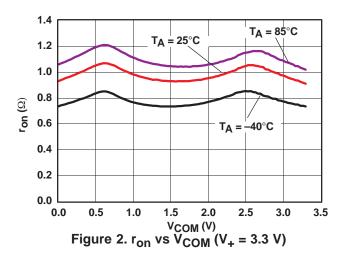
PARAMETER	SYMBOL	TEST COI	NDITIONS	T_A	V ₊	MIN	TYP	MAX	UNIT
Dynamic									
Turn-on time	tON	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 17	25°C Full	1.8 V 1.65 V to 1.95 V	3	38.5	85 90	ns
Turn-off time	tOFF	$V_{COM} = V_+,$ $R_L = 50 \Omega,$	C _L = 35 pF, See Figure 17	25°C Full	1.8 V 1.65 V to 1.95 V	2	8.5	16 18	ns
Break-before- make time	t _{BBM}	$V_{NO} = V_{+},$ $R_{L} = 50 \Omega,$	C _L = 35 pF, See Figure 18	25°C Full	1.8 V 1.65 V to 1.95 V	1	33	75 80	ns
Charge injection	QC	V _{GEN} = 0, R _{GEN} = 0,	C _L = 1 nF, See Figure 22	25°C	1.8 V		5		рС
NO OFF capacitance	C _{NO(OFF)}	V _{NO} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	1.8 V		18.5		pF
COM OFF capacitance	CCOM(OFF)	V _{COM} = V ₊ or GND, Switch OFF,	See Figure 16	25°C	1.8 V		55		pF
NO ON capacitance	C _{NO(ON)}	V _{NO} = V ₊ or GND, Switch ON,	See Figure 16	25°C	1.8 V		78		pF
COM ON capacitance	C _{COM(ON)}	V _{COM} = V ₊ or GND, Switch ON,	See Figure 16	25°C	1.8 V		78		pF
Digital input capacitance	Cl	$V_I = V_+ \text{ or GND},$	See Figure 16	25°C	1.8 V		3		pF
Bandwidth	BW	$R_L = 50 \Omega$, Switch ON,	See Figure 19	25°C	1.8 V		73		MHz
OFF isolation	O _{ISO}	$R_L = 50 \Omega$, f = 1 MHz,	Switch OFF, See Figure 20	25°C	1.8 V		-64		dB
Crosstalk	X _{TALK}	$R_L = 50 \Omega$, f = 1 MHz,	Switch ON, See Figure 21	25°C	1.8 V		-64		dB
Total harmonic distortion	THD	$R_L = 600 \Omega$, $C_L = 50 pF$,	f = 20 Hz to 20 kHz, See Figure 23	25°C	1.8 V		0.080		%
Supply									
Positive supply current	l ₊	$V_I = V_+$ or GND,	Switch ON or OFF	25°C Full	1.95 V		1	200	nA

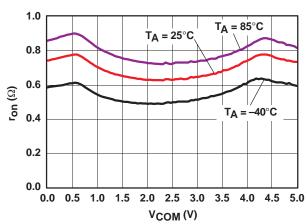
⁽¹⁾ The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

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TYPICAL PERFORMANCE







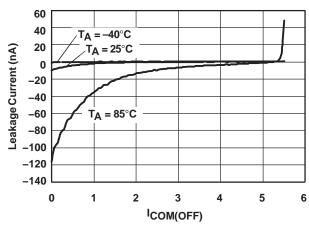
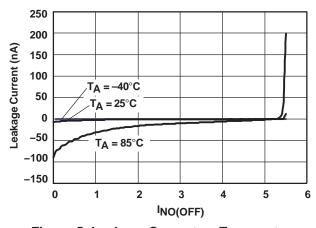


Figure 3. r_{on} vs V_{COM} ($V_{+} = 5 V$)

Figure 4. Leakage Current vs Temperature



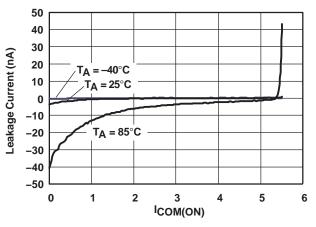


Figure 5. Leakage Current vs Temperature

Figure 6. Leakage Current vs Temperature



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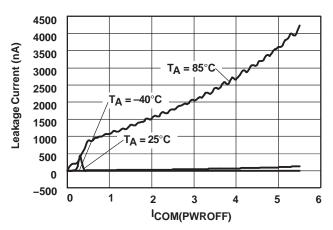


Figure 7. Leakage Current vs Temperature

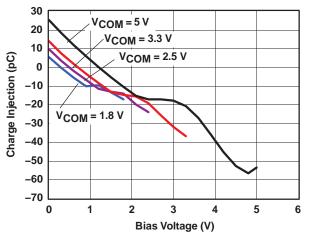


Figure 8. Charge Injection (Q_C) vs V_{COM}

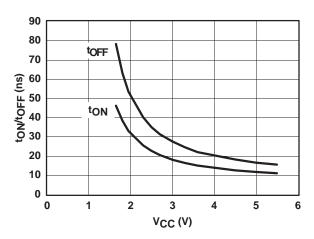


Figure 9. t_{ON} and t_{OFF} vs Supply Voltage

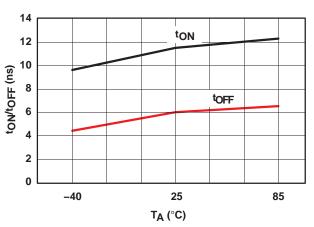


Figure 10. $t_{\mbox{ON}}$ and $t_{\mbox{OFF}}$ vs Temperature

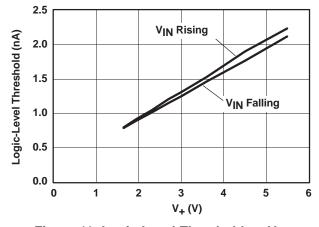


Figure 11. Logic-Level Threshold vs V₊

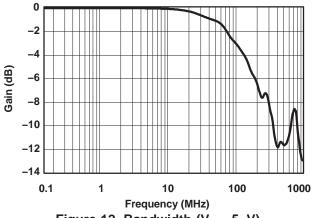
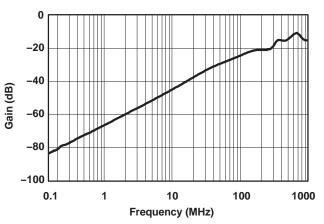


Figure 12. Bandwidth $(V_+ = 5 V)$



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0.010 0.009 800.0 0.007 0.006 0.005 0.004 0.003 0.002 0.001 0.000 0.01 0.1 1 10 100 Frequency (kHz)

Figure 13. OFF Isolation vs Crosstalk

Figure 14. Total Harmonic Distortion vs Frequency

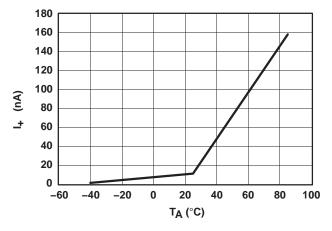


Figure 15. Power-Supply Current vs Temperature $(V_+ = 5 V)$



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PIN DESCRIPTION

PIN NUMBER	NAME	DESCRIPTION
1	NO0	Digital control pin to connect COM to NO
2	NO1	Normally open
3	NO2	Normally open
4	GND	Digital ground
5	IN2	Digital control pin to connect COM to NO
6	IN1	Digital control pin to connect COM to NO
7	COM	Common
8	V ₊	Power supply

PARAMETER DESCRIPTION

SYMBOL	DESCRIPTION
Vсом	Voltage at COM
VNO	Voltage at NO
ron	Resistance between COM and NO ports when the channel is ON
^r peak	Peak on-state resistance over a specified voltage range
Δr _{on}	Difference of ron between channels in a specific device
ron(flat)	Difference between the maximum and minimum value of ron in a channel over the specified range of conditions
I _{NO(OFF)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the OFF state under worst-case input and output conditions
INO(PWROFF)	Leakage current measured at the NO port during the power-down condition, $V_{+} = 0$
I _{NO(ON)}	Leakage current measured at the NO port, with the corresponding channel (NO to COM) in the ON state and the output (COM) open
ICOM(ON)	Leakage current measured at the COM port, with the corresponding channel (COM to NO) in the ON state and the output (NO) open
ICOM(OFF)	Leakage current measured at the COM port, with the corresponding channel (COM to NC) in the OFF state under worst-case input and output conditions
ICOM(PWROFF)	Leakage current measured at the COM port during the power-down condition, V ₊ = 0
VIH	Minimum input voltage for logic high for the control input (IN)
V _{IL}	Maximum input voltage for logic low for the control input (IN)
VI	Voltage at the control input (IN)
I _{IH} , I _{IL}	Leakage current measured at the control input (IN)
tON	Turn-on time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, or NO) signal when the switch is turning ON.
^t OFF	Turn-off time for the switch. This parameter is measured under the specified range of conditions and by the propagation delay between the digital control (IN) signal and analog output (COM, or NO) signal when the switch is turning OFF.
^t BBM	Break-before-make time. This parameter is measured under the specified range of conditions and by the propagation delay between the output of two adjacent analog channels (NC and NO) when the control signal changes state.
QC	Charge injection is a measurement of unwanted signal coupling from the control (IN) input to the analog (NO, or COM) output. This is measured in coulomb (C) and measured by the total charge induced due to switching of the control input. Charge injection, $Q_C = C_L \times \Delta V_{COM}$, C_L is the load capacitance, and ΔV_{COM} is the change in analog output voltage.



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PARAMETER DESCRIPTION (continued)

SYMBOL	DESCRIPTION
C _{NO(OFF)}	Capacitance at the NO port when the corresponding channel (NO to COM) is OFF
C _{NO(ON)}	Capacitance at the NO port when the corresponding channel (NO to COM) is ON
C _{COM(ON)}	Capacitance at the COM port when the corresponding channel (COM to NO) is ON
C _{COM(OFF)}	Capacitance at the COM port when the corresponding channel (COM to NO) is OFF
Cl	Capacitance of control input (IN)
O _{ISO}	OFF isolation of the switch is a measurement of OFF-state switch impedance. This is measured in dB in a specific frequency, with the corresponding channel (NO to COM) in the OFF state.
XTALK	Crosstalk is a measurement of unwanted signal coupling from an ON channel to an OFF channel (NC to NO or NO to NC). This is measured in a specific frequency and in dB.
BW	Bandwidth of the switch. This is the frequency in which the gain of an ON channel is -3 dB below the DC gain.
THD	Total harmonic distortion describes the signal distortion caused by the analog switch. This is defined as the ratio of root mean square (RMS) value of the second, third, and higher harmonic to the absolute magnitude of the fundamental harmonic.
I ₊	Static power-supply current with the control (IN) pin at V ₊ or GND



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PARAMETER MEASUREMENT INFORMATION

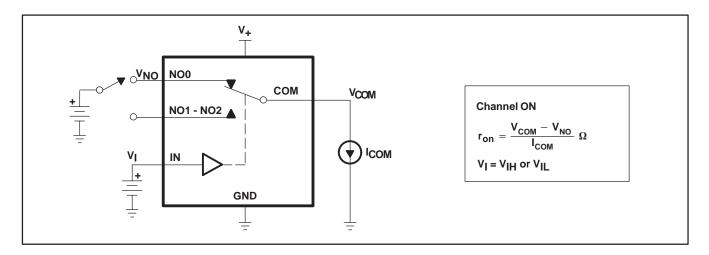


Figure 16. ON-State Resistance (ron)

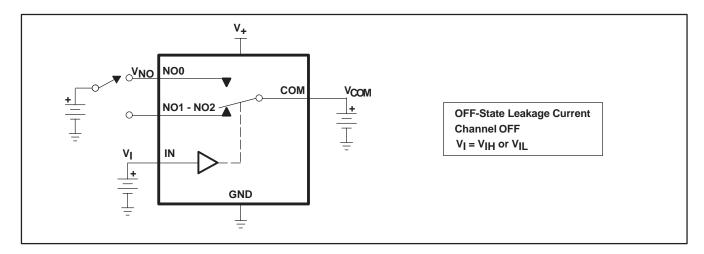


Figure 17. OFF-State Leakage Current (I_{NC(OFF)}, I_{NO(OFF)}, I_{NO(PWROFF)}, I_{COM(OFF)}, I_{COM(PWROFF)})

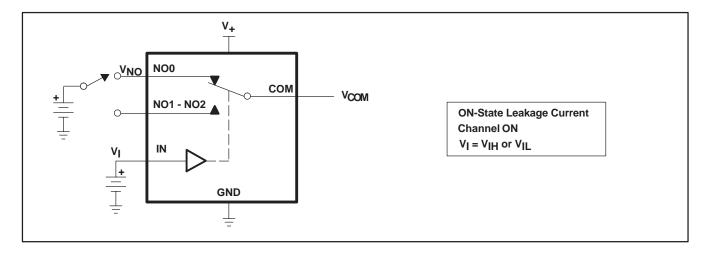


Figure 18. ON-State Leakage Current (I_{COM(ON)}, I_{NO(ON)})



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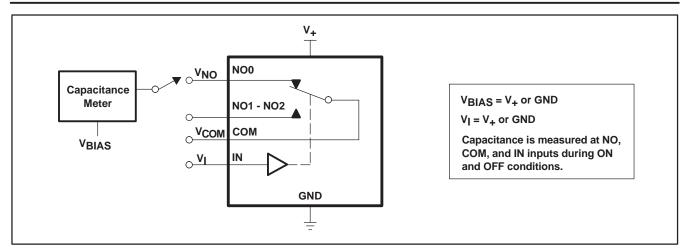
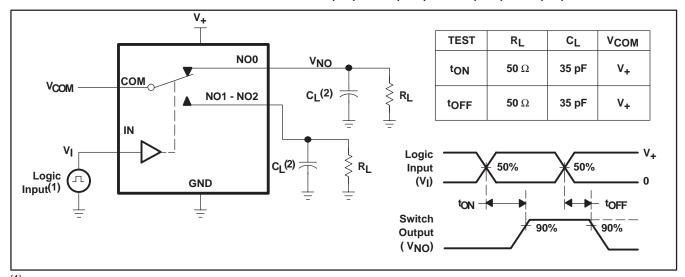
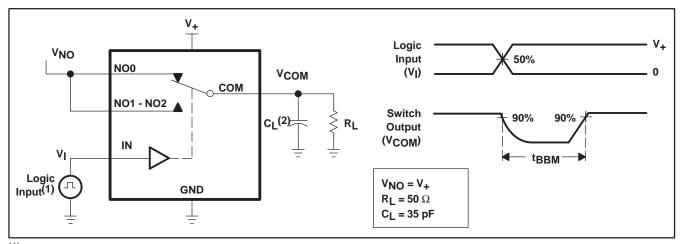


Figure 19. Capacitance (C_I, $C_{COM(ON)}$, $C_{NO(OFF)}$, $C_{COM(OFF)}$, $C_{NO(ON)}$)



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f < 5$ ns.
- (2) C_L includes probe and jig capacitance.

Figure 20. Turn-On (t_{ON}) and Turn-Off Time (t_{OFF})



- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , t_f < 5 ns. t_f < 5 ns.
- (2) C_L includes probe and jig capacitance.

Figure 21. Break-Before-Make Time (t_{BBM})



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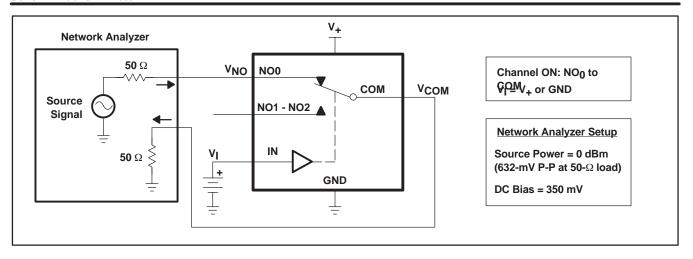


Figure 22. Bandwidth (BW)

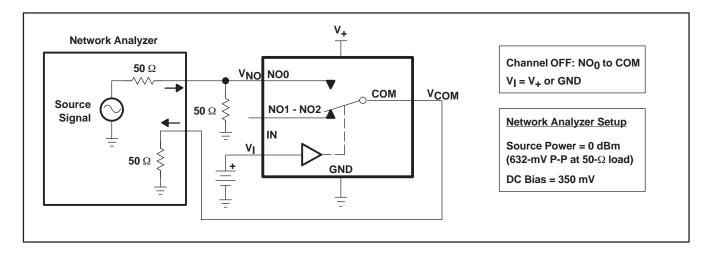


Figure 23. OFF Isolation (O_{ISO})

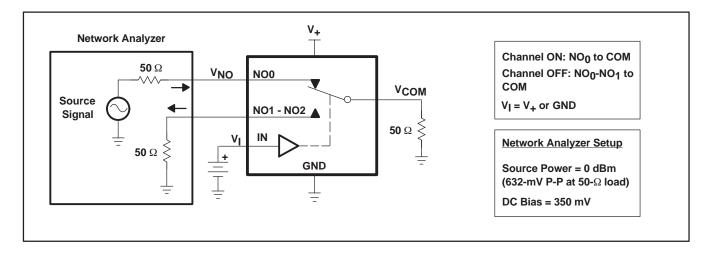
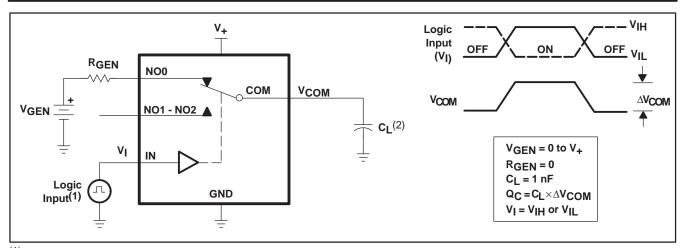


Figure 24. Crosstalk (X_{TALK})

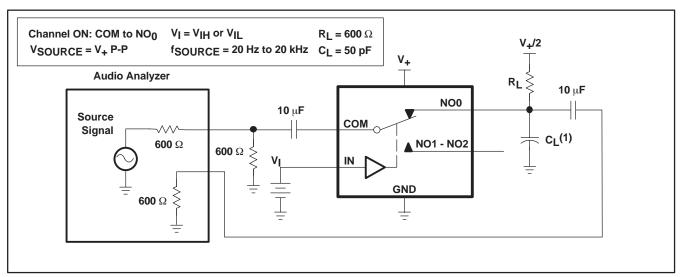


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- (1) All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f < 5$ ns.
- (2) C_L includes probe and jig capacitance.

Figure 25. Charge Injection (Q_C)



(1) C_L includes probe and jig capacitance.

Figure 26. Total Harmonic Distortion (THD)



PACKAGE OPTION ADDENDUM

27-Feb-2006

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
TS5A3359DCUR	ACTIVE	US8	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A3359DCURE4	ACTIVE	US8	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A3359DCUT	ACTIVE	US8	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TS5A3359DCUTE4	ACTIVE	US8	DCU	8	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

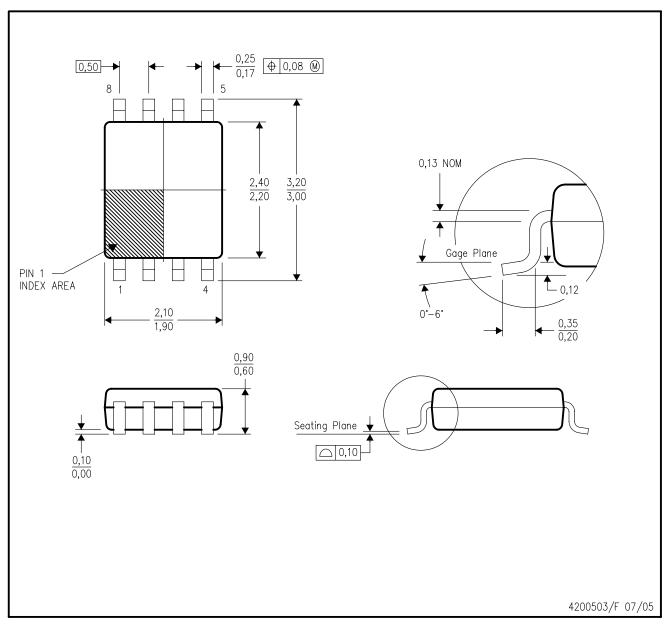
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-187 variation CA.



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